

Low Voltage, 300-MHz - 3 dB Bandwidth, SPDT Analog Switch with Power Down Protection

(2:1 Multiplexer/Demultiplexer Bus Switch)

DESCRIPTION

The DG3157A, DG3157B are high-speed single-pole double-throw, low voltage switch. Using sub-micro CMOS technology, the DG3157A, DG3157B achieves low on-resistance and negligible propagation delay. The DG3157A, DG3157B can handle both analog and digital signals and permits signals with amplitudes of up to V_{CC} to be transmitted in either direction. Select pin of control logic input can be over the V+. When the select pin is low, B_0 is connected to the output A pin. When the select pin is high, B_1 is connected to the output A pin. The path that is open will have a high-impedance state with respect to the output A pin. Break before make is guaranteed. The DG3157A has an internal pull down resistor on the control pin S, while the DG3157B does not.

FEATURES

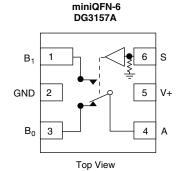
 Ultra small miniQFN6 package of 1 mm x 1.2 mm



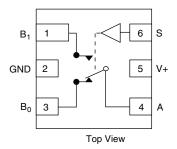
Wide operation voltage range: 1.8 V to 5.5 V $\,$

- RoHS*
- Useful in both analog and digital signal switching
- 300 MHz 3 dB bandwidth
- · Power down safe design
- Low voltage logic threshold:
 V_{th}(high) = 1.2 V at V+ = 3.3 V
- · Minimal propagation delay
- · Break-before-make switching
- Zero bounce in flow-through mode
- > 300 mA latch up current per JESD78
- > 8 kV ESD/HBM
- DG3157A version has internal pull down resistor on control pin S

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Device Marking: E miniQFN-6 DG3157B



Device Marking: D

TRUTH TABLE	
Logic Input (S)	Function
0	B ₀ Connected to A
1	B ₁ Connected to A

ORDERING INFORMATION						
Temp. Range	Part Number					
- 40 °C to 85 °C	miniQFN-6	DG3157ADN-T1-E4				
	IIIIIIQFN-0	DG3157BDN-T1-E4				

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

DG3157A, DG3157B

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ABSOLUTE MAXIMUM RATINGS						
Parameter		Limit	Unit			
Reference V+ to GND	- 0.3 to + 6	V				
S, A, B ^a	- 0.3 to (V+ + 0.3)	v				
Continuous Current (Any terminal)	± 50	mΛ				
Peak Current (Pulsed at 1 ms, 10 % duty cy	± 200	mA				
Storage Temperature	D-Suffix	- 65 to 150	°C			
Power Dissipation (Packages) ^b	miniQFN-6 ^c	160	mW			

Notes:

- a. Signals on A, or B or S exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 2.0 mW/°C above 70 °C.

		Test Conditions Unless Otherwise Specified $V+=3.0\ V,\ V_{SL}=0.5\ V,\ V_{SH}=2.0\ V^e$			Limits - 40 °C to 85 °C			
Parameter	Symbol			Temp.a	Min. ^b	Typ.c	Max. ^b	Unit
DC Characteristics								
		V+ = 1.65 to 1.95 V			1.2			
High Level Input Voltage	V_{SH}	V+ = 2.0 to 2.6 V]	1.4			
riigii zovoriiipat voltago	- 311	V+ = 2.7 to 3.6 V			2.0			
			= 4.5 to 5.5 V	Full	2.4			V
			= 1.65 to 1.95 V				0.3	
Low Level Input Voltage	V_{SL}		= 2.0 to 2.6 V				0.4	
g	OL		= 2.7 to 3.6 V]			0.5	
		V+	= 4.5 to 5.5 V				0.8	
			$V_{BN} = 0 \text{ V}, I_{A} = 30 \text{ mA}$			4.8	7	Ω
		V+ = 4.5 V	$V_{BN} = 2.4 \text{ V}, I_{A} = -30 \text{ mA}$			5.7	12	
	R _{ON}		$V_{BN} = 4.5 \text{ V}, I_{A} = -30 \text{ mA}$			10.3	15	
		V+ = 3.0 V	$V_{BN} = 0 \text{ V}, I_A = 24 \text{ mA}$	Full		5.9	9	
On-Resistance			$V_{BN} = 3.0 \text{ V}, I_A = -24 \text{ mA}$			13.7	20	
		V+ = 2.3 V	$V_{BN} = 0 \text{ V}, I_{A} = 8 \text{ mA}$			7	12	
			$V_{BN} = 2.3 \text{ V}, I_{A} = -8 \text{ mA}$			16.2	30	
		V+ = 1.65 V	$V_{BN} = 0 \text{ V}, I_{A} = 4 \text{ mA}$			9.2	20	
		V+= 1.65 V	$V_{BN} = 1.65 \text{ V}, I_A = -4 \text{ mA}$			24	50	
	R _{FLAT}	0 < V _{BN} < V+	$V+ = 4.5 \text{ V}, I_A = -30 \text{ mA}$	Room		8		
On-Resistance Flatness			$V+ = 3.0 \text{ V}, I_A = -24 \text{ mA}$			13		
On-nesistance matriess			$V+ = 2.3 \text{ V}, I_A = -8 \text{ mA}$			24		
			V+ = 1.65 V, I _A = - 4 mA			89		
	4 D	V+ = 4.5 V, V _{BN} = 3.15 V, I _A = - 30 mA		noom		0.8		
On-Resistance Matching Between Channels		V+ = 3.0 V, V _{BN} = 2.1 V, I _A = - 24 mA				0.1		
	ΔR_{ON}	V+ = 2.3 V, V _{BN} = 1.6 V, I _A = -8 mA				0.2		
		V+ = 1.65 V, V _{BN} = 1.15 V, I _A = - 4 mA				0.9		
Input Leakage Current	IS	V+ = 5.5 V, $V_A = 5.5 V,$ $V_S = 0.8 V, 2.4 V$	DG3157B	Full -	- 1.0		1.0	
,			DG3157A		- 1.0	2.5	7.0	
Off Stage Switch Leakage	I _{BN(off)}	$V+ = 5.5 \text{ V}, V_A/V_B = 0 \text{ V}/5.5 \text{ V}$		Room Full	- 0.1 - 1.0		0.1 1.0	μA
On State Switch Leakage	I _{BN(on)}	$V+ = 5.5 \text{ V}, V_A/V_B = 0 \text{ V}/5.5 \text{ V}$		Room Full	- 0.1 - 1.0		0.1 1.0	



SPECIFICATIONS								
		Test Conditions Unless Otherwise Specified $V+=3.0 \text{ V}, V_{SL}=0.5 \text{ V}, V_{SH}=2.0 \text{ V}^e$			Limits			
				_ a		0 °C to 85		
Parameter Power Supply	Symbol	V+ = 3.0 V, V _{SL} = 0.	.5 v, v _{SH} = 2.0 v	Temp. ^a	Min.b	Typ. ^c	Max.b	Unit
Power Supply Range	V+	T		Full	1.65	1	5.5	l v
		.,,		Room	1.03		1	
Quiescent Supply Current	l+	$V+ = 5.5 V, V_A =$	= V+ or GND	Full			10	μΑ
AC Electrical Characteristice								
			V+ = 1.65 to 1.95 V	Full		1.5		
Prop Delay Time ^f	t _{PHL} /t _{PLH}	V _A = 0 V	V+ = 2.3 to 2.7 V	Full		0.8		
Trop Delay Time	THE TEN	A S	V+ = 3.0 to 3.6 V	Full		0.4		
			V+ = 4.5 to 5.5 V	Full		0.3		
			V+ = 1.65 to 1.95 V	Room Full		27	50	
Outside Freehle Timef	t _{PZL} /t _{PZH}	$V_{LOAD} = 2 \times V + \text{ for } t_{PZL}$	V+ = 2.3 to 2.7 V	Room Full		15	45	
Output Enable Time [†]	'PZL''PZH	V _{LOAD} = 0 V for t _{PZH}	V+ = 3.0 to 3.6 V	Room Full		10	30	
			V+ = 4.5 to 5.5 V	Room Full		7	25	
		$V_{LOAD} = 2 \times V + \text{ for } t_{PLZ}$ $V_{LOAD} = 0 \text{ V for } t_{PHZ}$	V+ = 1.65 to 1.95 V	Room Full		16	45	ns
			V+ = 2.3 to 2.7 V	Room Full		10	40	
Output Disable Time ^f	t _{PLZ} /t _{PHZ}		V+ = 3.0 to 3.6 V	Room		8	35	
			V+ = 4.5 to 5.5 V	Room		6	21	
		V+ = 1.65 t	V+ = 1.65 to 1.95 V		0.5	11		
d		V+ = 2.3 to 2.7 V		Full	0.5	6		
Break-Before-Make Time ^d	t _{BBM}	V+ = 3.0 to 3.65		Full	0.5	4		1
		V+ = 4.5 to 5.5 V		Full	0.5	3		
Ola a constant and	Q	C _L = 1 nF, V _{GEN} = 0 V	V+ = 5 V	Room		7		20
Charge Injection ^d	Q	$R_{GEN} = 0 \Omega$	V+ = 3.3 V	Room		5		рC
Off Isolation ^d	OIRR	P = 50 O f	_ 10 MU-	Room		- 57		40
Crosstalk ^d	X _{TALK}	$R_L = 50 \Omega$, f	- IO WII IZ	Room		- 64		dB
- 3 dB Bandwidth ^d	BW	$R_L = 50 \Omega$		Room		300		MHz
Total Harmonic Distortion ^d	THD	$R_L = 600 \Omega$, 0.5 Vp-p f = 600 Hz - 20 kHz		Room		0.016		%
Capacitance		1		<u> </u>				
Control Pin Capacitanced	C _S	V+ =	0 V	Room		3.7		
B Port Off Capacitance ^d	C _{IO-B}			Room		7		pF
A Port Capacitance When Switch Enable ^d	C _{IO-A(on)}	V+ = 5 V		Room		19		, pi

Notes:

- a. Room = 25 $^{\circ}\text{C},\,\text{Full}$ = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V_S = input voltage to perform proper function.
- f. Guaranteed by design and not production tested. The bus switch propagation delay is a function of the RC time constant contributed by the on-resistance and the specified load capacitance with an ideal voltage source (zero output impedance) driving the switch.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

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LOGIC DIAGRAM Positive Logic

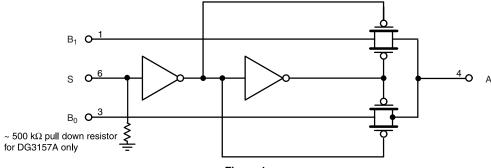


Figure 1.

AC LOADING AND WAVEFORMS

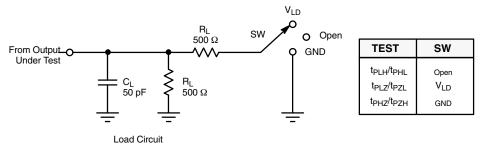


Figure 2. AC Test Circuit

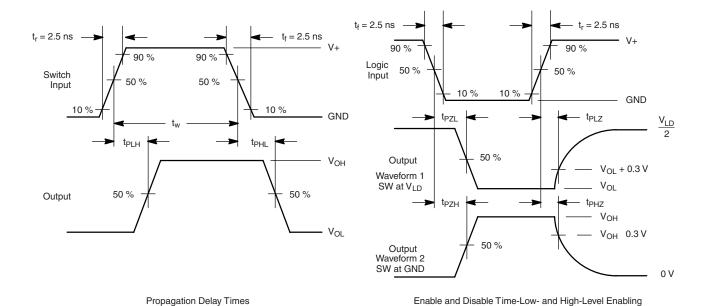


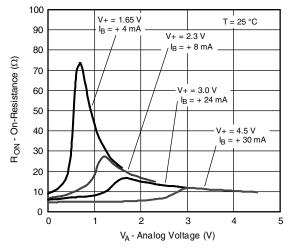
Figure 3. AC Waveforms

Notes:

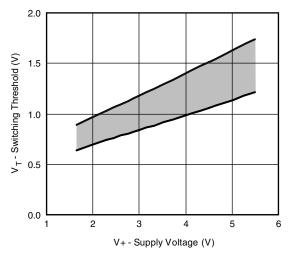
- C_L includes probe and jig capacitance.
- Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control.
- Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: Input PRR = 1.0 MHz, t_w = 500 ns.
- The outputs are measured one at a time with one transition per measurement.
- V_{LD} = 2 V+.



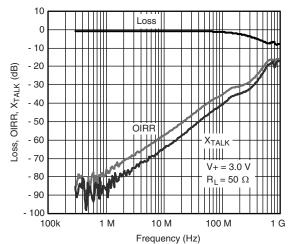
TYPICAL CHARACTERISTICS $T_A = 25$ °C, unless otherwise noted



 R_{ON} vs. V_A and Supply Voltage



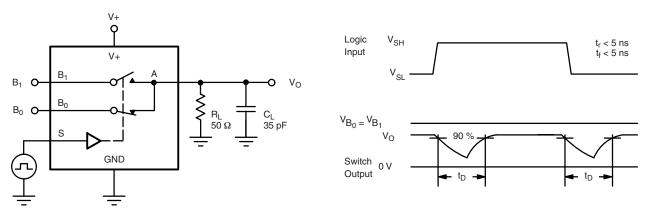
Switching Threshold vs. Supply Voltage



Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

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TEST CIRCUITS



C_L (includes fixture and stray capacitance)

Figure 4. Break-Before-Make Interval

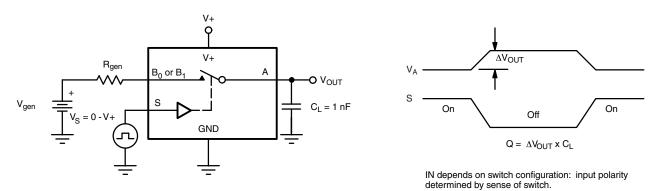


Figure 5. Charge Injection

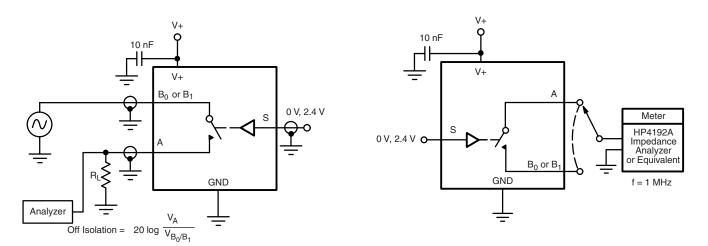


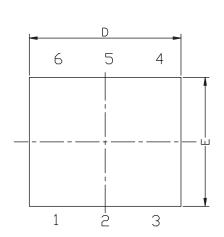
Figure 6. Off-Isolation

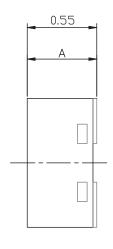
Figure 7. Channel Off/On Capacitance

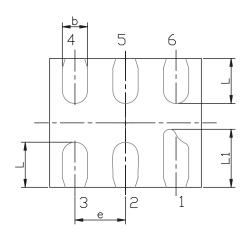
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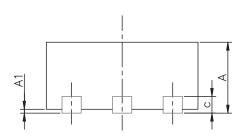


MINI QFN-6L CASE OUTLINE







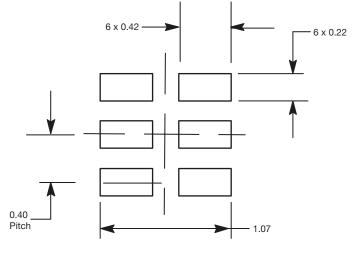


DIM	M	IILLIMETER	S	INCHES			
Dilvi	MIN.	NAM.	MAX.	MIN.	NAM.	MAX.	
Α	0.50	0.55	0.60	0.0197	0.0217	0.0236	
A1	0.00	-	0.05	0.000	-	0.002	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С		0.15 REF			0.006 REF		
D	1.15	1.20	1.25	0.045	0.047	0.049	
E	0.95	1.00	1.05	0.037	0.039	0.041	
е		0.40 BSC			0.016 BSC		
L	0.30	0.35	0.40	0.012	0.014	0.016	
L1	0.40	0.45	0.50	0.016	0.018	0.020	

ECN T-07039-Rev. A, 12-Feb-07 DWG: 5958



RECOMMENDED MINIMUM PADS FOR MINI QFN 6L



Mounting Footprint Dimensions in mm



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